



AWT6134

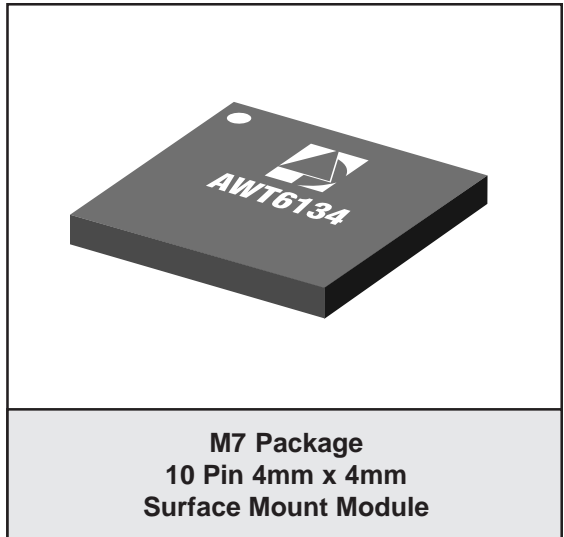
KPCS/CDMA 3.4V/28dBm
 Linear Power Amplifier Module
 PRELIMINARY DATA SHEET - Rev 1.0

FEATURES

- InGaP HBT Technology
- High Efficiency: 39%
- Low Quiescent Current: 48 mA
- Low Leakage Current in Shutdown Mode: <math><1 \mu A</math>
- $V_{REF} = +2.8 V$ (+2.7 V min over temp)
- Optimized for a 50 Ω System
- Low Profile Miniature Surface Mount Package: 1.56mm Max
- CDMA 1XRTT Compliant
- CDMA 1xEV-DO Compliant

APPLICATIONS

- Korean PCS CDMA Wireless Handsets



PRODUCT DESCRIPTION

The AWT6134 meets the increasing demands for higher efficiency and linearity in CDMA 1XRTT handsets. The PA module is optimized for $V_{REF} = +2.8 V$, a requirement for compatibility with the Qualcomm 6000 chipset. The device is manufactured on an advanced InGaP HBT MMIC technology offering state-of-the-art reliability, temperature stability, and

ruggedness. Selectable bias modes that optimize efficiency for different output power levels, and a shutdown mode with low leakage current, increase handset talk and standby time. The self-contained 4mm x 4mm surface mount package incorporates matching networks optimized for output power, efficiency, and linearity in a 50 Ω system.

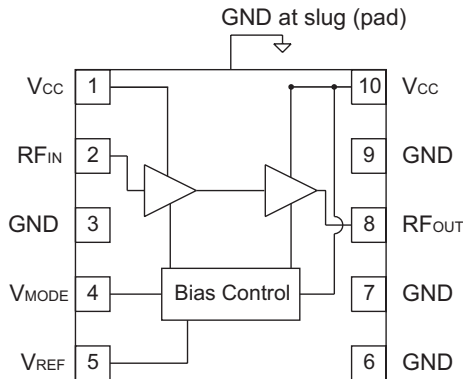


Figure 1: Block Diagram

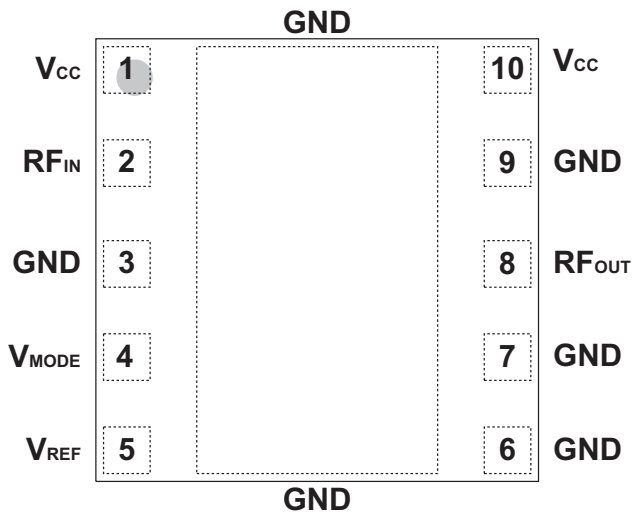


Figure 2: Pinout (X-ray Top View)

Table 1: Pin Description

PIN	NAME	DESCRIPTION
1	V_{CC}	Supply Voltage
2	RF_{IN}	RF Input
3	GND	Ground
4	V_{MODE}	Mode Control Voltage
5	V_{REF}	Reference Voltage
6	GND	Ground
7	GND	Ground
8	RF_{OUT}	RF Output
9	GND	Ground
10	V_{CC}	Supply Voltage

ELECTRICAL CHARACTERISTICS**Table 2: Absolute Minimum and Maximum Ratings**

PARAMETER	MIN	MAX	UNIT
Supply Voltage (V_{CC})	0	+5	V
Mode Control Voltage (V_{MODE})	0	+3.5	V
Reference Voltage (V_{REF})	0	+3.5	V
RF Input Power (P_{IN})	-	+10	dBm
Storage Temperature (T_{STG})	-40	+150	°C

Stresses in excess of the absolute ratings may cause permanent damage. Functional operation is not implied under these conditions. Exposure to absolute ratings for extended periods of time may adversely affect reliability.

Table 3: Operating Ranges

PARAMETER	MIN	TYP	MAX	UNIT	COMMENTS
Operating Frequency (f)	1750	-	1780	MHz	
Supply Voltage (V_{CC})	+3.2	+3.4	+4.2	V	
Reference Voltage (V_{REF})	+2.7 0	+2.8 -	+3.1 +0.5	V	PA "on" PA "shut down"
Mode Control Voltage (V_{MODE})	+2.5 0	+2.8 -	+3.1 +0.5	V	Low Bias Mode High Bias Mode
RF Output Power (P_{OUT})	+27.5 ⁽¹⁾	+28.0	-	dBm	
Case Temperature (T_C)	-30	-	+85	°C	

The device may be operated safely over these conditions; however, parametric performance is guaranteed only over the conditions defined in the electrical specifications.

Notes:

(1) For operation at $T_C = +85$ °C and $V_{CC} = +3.2$ V, P_{OUT} is derated by 0.5 dB.

Table 4: Electrical Specifications

(T_C = +25 °C, V_{CC} = +3.4 V, V_{REF} = +2.8 V, 50 Ω system)

PARAMETER	MIN	TYP	MAX	UNIT	COMMENTS
Gain	24 21	26 23.5	29 27	dB	P _{OUT} = +28 dBm, V _{MODE} = 0 V P _{OUT} = +16 dBm, V _{MODE} = +2.8 V
Adjacent Channel Power ⁽¹⁾ at ±1.25 kHz offset Primary Channel BW = 1.23 MHz Adjacent Channel BW = 30 kHz	- -	-49 -52	-46.5 -46.5	dBc	P _{OUT} = +28 dBm, V _{MODE} = 0 V P _{OUT} = +16 dBm, V _{MODE} = +2.8 V
Adjacent Channel Power ⁽¹⁾ at ±2.25 MHz offset Primary Channel BW = 1.23 MHz Adjacent Channel BW = 30 kHz	- -	-60 -68	-57 -57	dBc	P _{OUT} = +28 dBm, V _{MODE} = 0 V P _{OUT} = +16 dBm, V _{MODE} = +2.8 V
Power-Added Efficiency ⁽¹⁾	37 8	39 9	- -	%	P _{OUT} = +28 dBm, V _{MODE} = 0 V P _{OUT} = +16 dBm, V _{MODE} = +2.8 V
Quiescent Current (I _q)	-	48	60	mA	V _{MODE} = +2.8 V
Reference Current	-	3.5	5	mA	through V _{REF} pin, PA "on"
Mode Control Current	-	0.3	0.5	mA	through V _{MODE} pin, V _{MODE} = +2.8 V
Leakage Current	-	<1	5	μA	V _{CC} = +4.2 V, V _{REF} = 0 V V _{MODE} = 0 V
Noise in Receive Band 1840 MHz to 1870 MHz	- -	-137 -141	-135 -138	dBm/Hz	P _{OUT} = +28 dBm, V _{MODE} = 0 V P _{OUT} = +16 dBm, V _{MODE} = +2.8 V
Harmonics 2fo 3fo, 4fo	- -	-45 -55	-30 -30	dBc	P _{OUT} ≤ +28 dBm
Input Impedance	-	-	2:1	VSWR	
Spurious Output Level (all spurious outputs)	-	-	-65	dBc	P _{OUT} ≤ +28 dBm In-band load VSWR < 8:1 Out-of-band load VSWR < 8:1 Applies over all voltage and temperature operating ranges
Load mismatch stress with no permanent degradation or failure	8:1	-	-	VSWR	V _{CC} = +5.0 V, P _{IN} = +5 dBm Applies over full operating temperature range

Notes:

(1) ACPR and PAE limits apply to middle frequency only.

Table 5: Electrical Specifications

(T_c = +25 °C, V_{CC} = +3.4 V, V_{REF} = +2.9 V, V_{MODE} = +2.9 V, 50 Ω system)

PARAMETER	MIN	TYP	MAX	UNIT	COMMENTS
Gain	23.5 20	25 23.5	28 27	dB	P _{OUT} = +28 dBm P _{OUT} = +16 dBm
Adjacent Channel Power ⁽¹⁾ at ±1.25 kHz offset Primary Channel BW = 1.23 MHz Adjacent Channel BW = 30 kHz	- -	-50 -52	-46.5 -46.5	dBc	P _{OUT} = +28 dBm P _{OUT} = +16 dBm
Adjacent Channel Power ⁽¹⁾ at ±2.25 MHz offset Primary Channel BW = 1.23 MHz Adjacent Channel BW = 30 kHz	- -	-58 -68	-56 -57	dBc	P _{OUT} = +28 dBm P _{OUT} = +16 dBm
Power-Added Efficiency ⁽¹⁾	37 8	40 9	- -	%	P _{OUT} = +28 dBm P _{OUT} = +16 dBm
Quiescent Current (I _q)	-	56	68	mA	V _{REF} = +2.9 V
Reference Current	-	3.5	5	mA	through V _{REF} pin, PA "on"
Mode Control Current	-	0.3	0.5	mA	through V _{MODE} pin
Leakage Current	-	<1	5	μA	V _{CC} = +4.2 V, V _{REF} = 0 V V _{MODE} = 0 V
Noise in Receive Band 1840 MHz to 1870 MHz	-	-135	-133	dBm/Hz	P _{OUT} = +28 dBm, V _{MODE} = +2.8 V
Harmonics 2fo 3fo, 4fo	- -	-45 -55	-30 -30	dBc	
Input Impedance	-	-	2:1	VSWR	
Spurious Output Level (all spurious outputs)	-	-	-65	dBc	P _{OUT} ≤ +28 dBm In-band load VSWR < 8:1 Out-of-band load VSWR < 8:1 Applies over all voltage and temperature operating ranges
Load mismatch stress with no permanent degradation or failure	8:1	-	-	VSWR	V _{CC} = +5.0 V, P _N = +5 dBm Applies over full operating temperature range

Notes:

(1) ACPR and PAE limits apply to middle frequency only.

APPLICATION INFORMATION

To ensure proper performance, refer to all related Application Notes on the ANADIGICS web site: <http://www.anadigics.com>

Shutdown Mode

The power amplifier may be placed in a shutdown mode by applying logic low levels (see Operating Ranges table) to both the V_{REF} and V_{MODE} voltages.

Bias Modes

The power amplifier may be placed in either a Low Bias mode or a High Bias mode by applying the appropriate logic level (see Operating Ranges table) to the V_{MODE} voltage. The Bias Control table lists the recommended modes of operation for various applications.

Table 6: Bias Control

APPLICATION	P _{OUT} LEVELS	BIAS MODE	V _{REF}	V _{MODE}
CDMA - low power	≤+16dBm	Low	+2.8 V	+2.8 V
CDMA - high power	>+16 dBm	High	+2.8 V	0 V
Shutdown	-	Shutdown	0 V	0 V

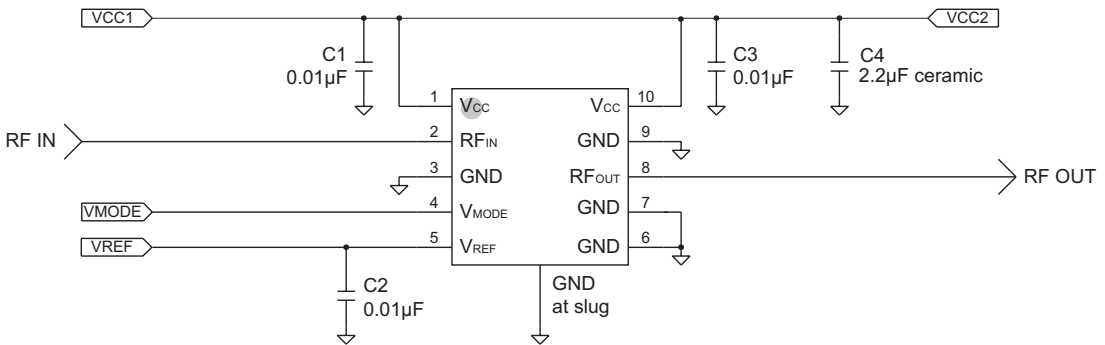
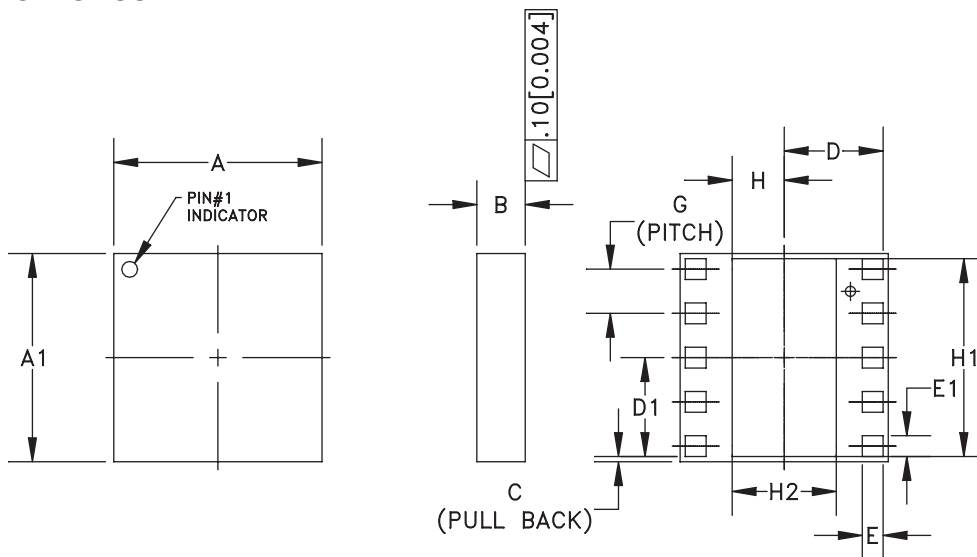


Figure 3: Application Circuit Schematic



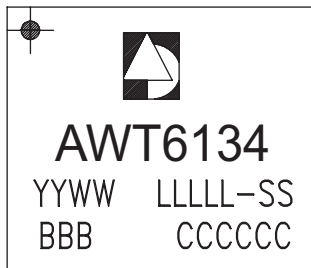
Symbol	MILLIMETERS			INCHES			NOTE
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
A	3.88	4.00	4.12	0.152	0.157	0.162	-
A1	3.88	4.00	4.12	0.152	0.157	0.162	-
B	1.26	1.41	1.56	0.049	0.055	0.061	-
C	-	0.10	-	-	0.004	-	-
D	-	1.90	-	-	0.075	-	-
D1	-	1.90	-	-	0.075	-	-
E	0.35	0.40	0.45	0.013	0.015	0.017	-
E1	0.35	0.40	0.45	0.013	0.015	0.017	-
G	0.85 BSC			0.033 BSC			-
H	-	1.00	-	-	0.039	-	-
H1	-	3.80	-	-	0.149	-	-
H2	-	2.00	-	-	0.078	-	-

NOTES:

1. CONTROLLING DIMENSIONS: MILLIMETERS
2. UNLESS SPECIFIED TOLERANCE=±0.076[0.003].

Figure 4: M7 Package Outline - 10 Pin 4mm x 4mm Surface Mount Module

TOP BRAND

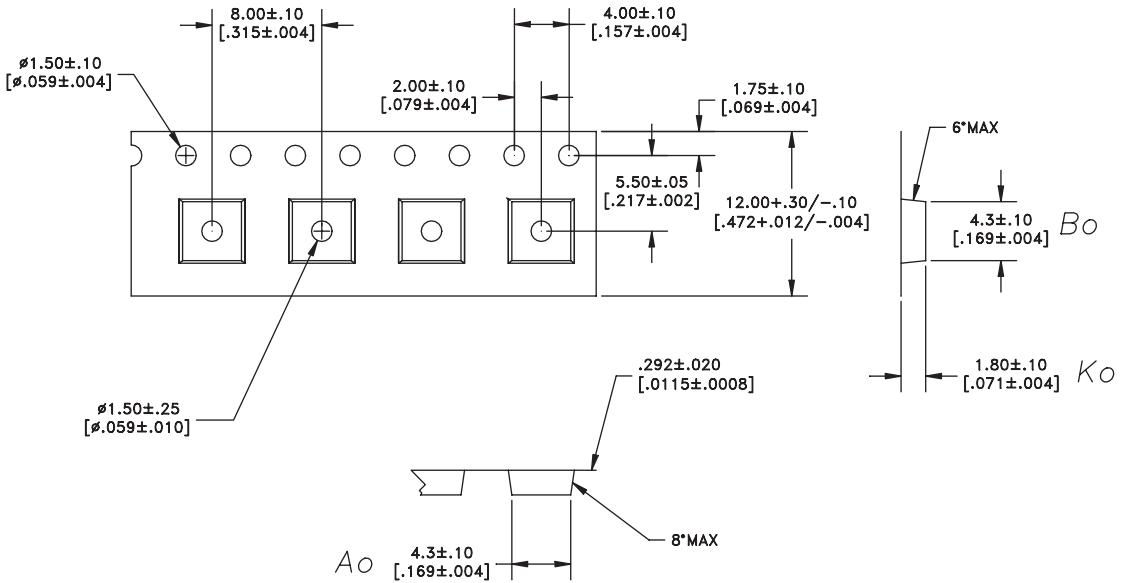


NOTES:

1. ANADIGICS LOGO SIZE: X=0.040±0.010 Y=0.048±0.010
2. PART # AWT6134
3. YEAR AND WORK WEEK: YYWW: YY = YEAR, WW = WORK WEEK
4. LOT - WAFER I.D.: LLLLL - SS = WAFER/LOT I.D.
5. PIN 1 INDICATOR: MOLD NOTCH -or- INK DOT
6. BOM # BBB
7. COUNTRY CODE: CCCCC
8. TYPE : ELITE
SIZE : AS LARGE AS POSSIBLE
LASER MARKED

Figure 5: Branding Specification

COMPONENT PACKAGING



DIMENSIONS ARE IN MILLIMETERS [INCHES]
STANDARD TOLERANCES

Figure 6: Tape & Reel Packaging

Table 7: Tape & Reel Dimensions

PACKAGE TYPE	TAPE WIDTH	POCKET PITCH	REEL CAPACITY	MAX REEL DIA
4mm X 4mm	12mm	8mm	2500	13"

NOTES

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ORDERING INFORMATION

ORDER NUMBER	TEMPERATURE RANGE	PACKAGE DESCRIPTION	COMPONENT PACKAGING
AWT6134M7P8	-30 °C to +110 °C	10 Pin 4mm x 4mm Surface Mount Module	Tape and Reel, 2500 pieces per Reel



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